

Docket No. 210148US99

IN RE APPLICATION OF: Jamal RAMDANI, et al.

SERIAL NO: 09/885,409

FILED: June 21, 2001

FOR: METHOD FOR FABRICATING A SEMICONDUCTOR STRUCTURE INCLUDING A METAL OXIDE INTERFACE WITH SILICON



COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Transmitted herewith is an amendment in the above-identified application.

- ☐ No additional fee is required
- ☐ Small entity status of this application under 37 C.F.R. §1.9 and §1.27 is claimed.
- ☒ Additional documents filed herewith: Request for Extension of Time (three-month)

The Fee has been calculated as shown below:

CLAIMS	CLAIMS REMAINING		HIGHEST NUMBER PREVIOUSLY PAID	NO. EXTRA CLAIMS	RATE	CALCULATIONS
TOTAL	6	MINUS	20	0	x \$18 =	\$0.00
INDEPENDENT	3	MINUS	3	0	x \$84 =	\$0.00
		<input type="checkbox"/> MULTIPLE DEPENDENT CLAIMS			+ \$280 =	\$0.00
		TOTAL OF ABOVE CALCULATIONS				\$0.00
		<input type="checkbox"/> Reduction by 50% for filing by Small Entity				\$0.00
		<input type="checkbox"/> Recordation of Assignment			+ \$40 =	\$0.00
		TOTAL				\$0.00

☒ A check in the amount of **\$930.00** is attached.

☒ Please charge any additional Fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.

☒ If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time may be charged to Deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.

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DOCKET NO: 210148US99



IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :

JAMAL RAMDANI ET AL : EXAMINER: SIMKOVIC,

SERIAL NO: 09/885,409 :

FILED: JUNE 21, 2001 : GROUP ART UNIT: 2812

FOR: METHOD FOR FABRICATING A
SEMICONDUCTOR STRUCTURE
INCLUDING A METAL OXIDE
INTERFACE WITH SILICON :

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AMENDMENT

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Responsive to the Official Action dated February 4, 2003, please enter the following amendment.

Amendments to the Claims appear at page 2 of this paper.

Remarks appear at page 6 of this paper.